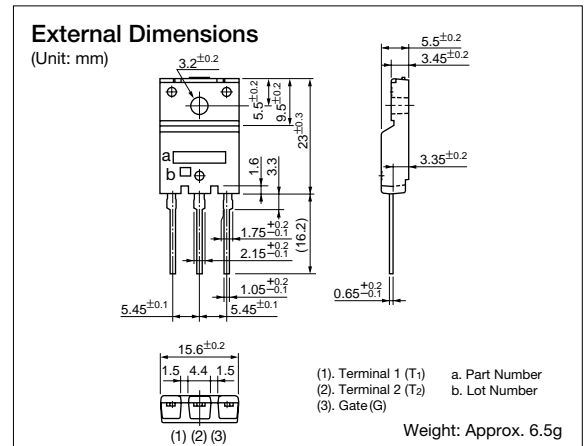


TO-3PF 12A Triac

TM1262B-R

■ Features

- Repetitive peak off-state voltage: $V_{DRM}=600V$
- RMS on-state current: $I_{T(RMS)}=12A$
- Gate trigger current: $I_{GT}=8mA$ max (MODE I, II, III)
- Isolation voltage: $V_{ISO}=2000V(AC, 1min.)$
- For resistive load
- UL approved type available



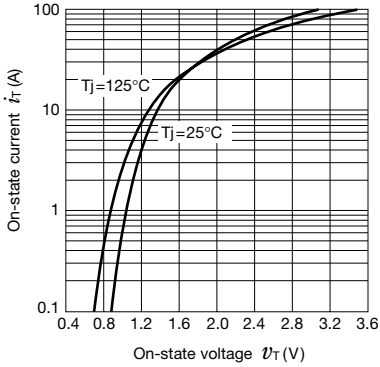
■ Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit	Conditions
Repetitive peak off-state voltage	V_{DRM}	600	V	$R_{GK}=\infty$, $T_J=-40^{\circ}C$ to $+125^{\circ}C$
RMS on-state current	$I_{T(RMS)}$	12	A	Conduction angle 360° , $T_C=98^{\circ}C$
Surge on-state current	I_{TSM}	120	A	50Hz full-cycle sine wave, Peak value, Non-repetitive, $T_J=125^{\circ}C$
Peak gate current	I_{GM}	2	A	$f \geq 50Hz$, duty $\leq 10\%$
Peak gate power loss	P_{GM}	5	W	$f \geq 50Hz$, duty $\leq 10\%$
Average gate power loss	$P_{G(AV)}$	0.5	W	
Junction temperature	T_J	-40 to $+125$	$^{\circ}C$	
Storage temperature	T_{stg}	-40 to $+125$	$^{\circ}C$	
Isolation voltage	V_{ISO}	2000	Vrms	50Hz Sine wave, RMS, Terminal to Case, 1 min.

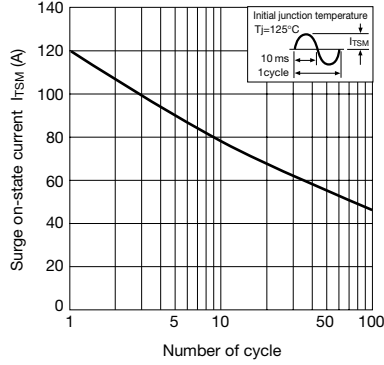
■ Electrical Characteristics

Parameter	Symbol	Ratings			Unit	Conditions		
		min	typ	max				
Off-state current	I_{DRM}		0.3	2.0	mA	$V_D=V_{DRM}$, $R_{GK}=\infty$, $T_J=125^{\circ}C$		
				0.1		$V_D=V_{DRM}$, $R_{GK}=\infty$, $T_J=25^{\circ}C$		
On-state voltage	V_{TM}			1.6	V	$I_{TM}=16A$, $T_C=25^{\circ}C$		
Gate trigger voltage	I	V _{GT}	0.8	1.1	1.8	V	$V_D=20V$, $R_L=40\Omega$, $T_C=25^{\circ}C$	T_2^+ , G^+
			0.4	0.6	1.2			T_2^+ , G^-
			0.4	0.7	1.2			T_2^-, G^-
				2.1				T_2^-, G^+
Gate trigger current	I	I _{GT}	2.0	5.0	8.0	mA	$V_D=20V$, $R_L=40\Omega$, $T_C=25^{\circ}C$	T_2^+ , G^+
			2.0	4.5	8.0			T_2^+ , G^-
			2.0	5.0	8.0			T_2^-, G^-
				25				T_2^-, G^+
Gate non-trigger voltage	V_{GD}	0.1			V	$V_D=1/2 \times V_{DRM}$, $T_J=125^{\circ}C$		
Holding current	I_H		6		mA	$T_J=25^{\circ}C$		
Thermal resistance	R_{th}			2.0	$^{\circ}C/W$	Junction to case		

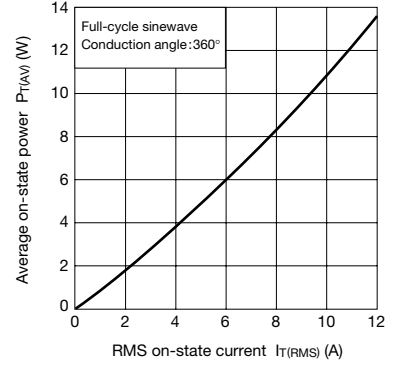
$V_T - I_T$ Characteristics (max)



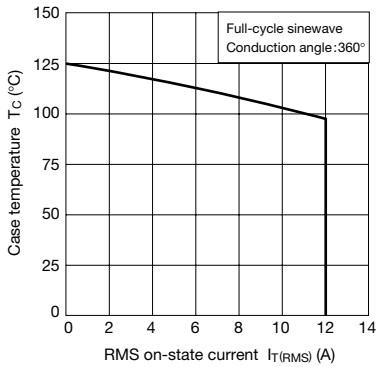
I_{rsm} Ratings



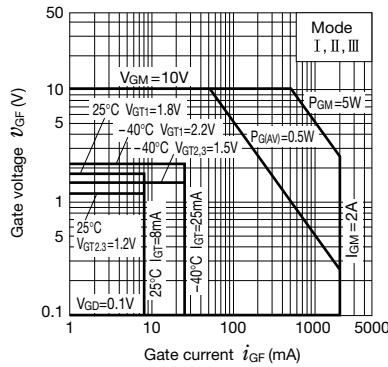
I_{T(RMS)} - P_{T(AV)} Characteristics



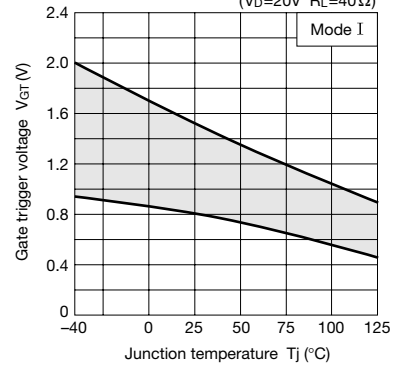
I_{T(RMS)} - T_c Ratings



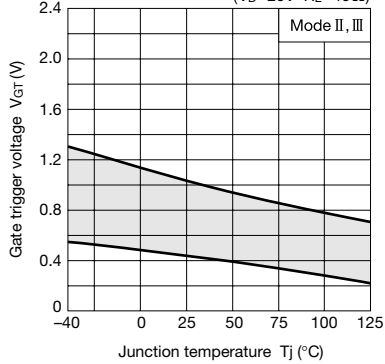
Gate Characteristics



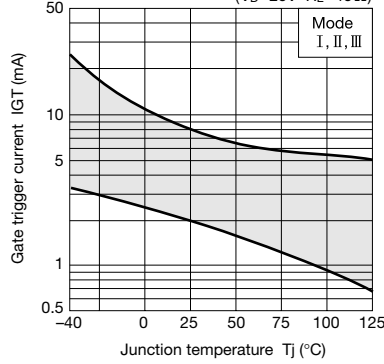
V_{GT} temperature characteristics (Typical)



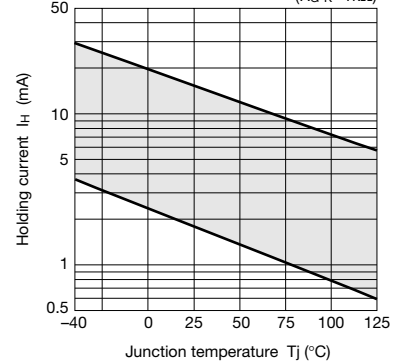
V_{GT} (Mode II, III) temperature characteristics (Typical)



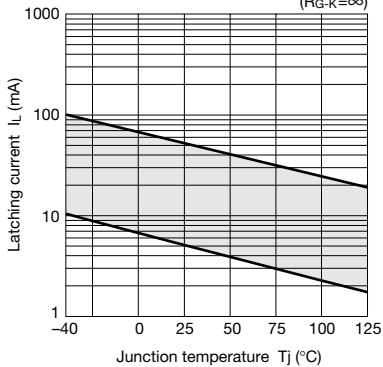
I_{GT} temperature characteristics (Typical)



I_H temperature characteristics (Typical)



I_L temperature characteristics (Typical)



r_{th(j-c)} - t Characteristics

